#### **Triacs**

#### **Silicon Bidirectional Thyristors**

Designed primarily for full-wave ac control applications, such as light dimmers, motor controls, heating controls and power supplies; or wherever full-wave silicon gate controlled solid-state devices are needed. Triac type thyristors switch from a blocking to a conducting state for either polarity of applied main terminal voltage with positive or negative gate triggering.

- Blocking Voltage to 800 Volts
- All Diffused and Glass Passivated Junctions for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Gate Triggering Guaranteed in Four Modes
- **%** Indicates UL Registered File #E69369
- Device Marking: Logo, Device Type, e.g., MAC210A8FP, Date Code

#### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off–State Voltage <sup>(1)</sup> (T <sub>J</sub> = -40 to +125°C, Sine Wave, 50 to 60 Hz, Gate Open)	VDRM, VRRM		Volts
MAC210A8FP MAC210A10FP		600 800	
On-State RMS Current (T <sub>C</sub> = +70°C)(2) Full Cycle Sine Wave 50 to 60 Hz	IT(RMS)	10	Amps
Peak Non-repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T <sub>C</sub> = +70°C) Preceded and followed by rated current	ITSM	100	Amps
Circuit Fusing Consideration (t = 8.3 ms)	I <sup>2</sup> t	40	A <sup>2</sup> s
Peak Gate Power (T <sub>C</sub> = +70°C, Pulse Width = 10 μs)	PGM	20	Watts
Average Gate Power (T <sub>C</sub> = +70°C, t = 8.3 ms)	PG(AV)	0.35	Watt
Peak Gate Current (T <sub>C</sub> = +70°C, Pulse Width = 10 μsec)	I <sub>GM</sub>	2.0	Amps
RMS Isolation Voltage ( $T_A = 25^{\circ}C$ , Relative Humidity $\leq 20\%$ ) (%)	V(ISO)	1500	Volts
Operating Junction Temperature Range	TJ	-40 to +125	°C
Storage Temperature Range	T <sub>stg</sub>	-40 to +150	°C

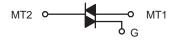
- (1) VDRM and VRRM for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.
- (2) The case temperature reference point for all T<sub>C</sub> measurements is a point on the center lead of the package as close as possible to the plastic body.



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# ISOLATED TRIAC (9\) 10 AMPERES RMS 600 thru 800 VOLTS





ISOLATED TO-220 Full Pack CASE 221C STYLE 3

PIN ASSIGNMENT			
1	Main Terminal 1		
2	Main Terminal 2		
3	Gate		

#### ORDERING INFORMATION

Device	Device Package	
MAC210A8FP	ISOLATED TO220FP	500/Box
MAC210A10FP	ISOLATED TO220FP	500/Box

#### THERMAL CHARACTERISTICS

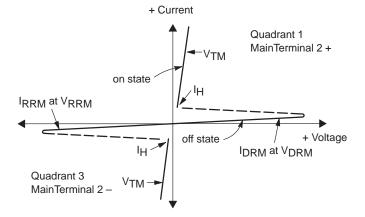
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{ heta JC}$	2.2	°C/W
Thermal Resistance, Case to Sink	$R_{\theta}CS$	2.2 (typ)	°C/W
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	60	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	TL	260	°C

#### **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted; Electricals apply in both directions)

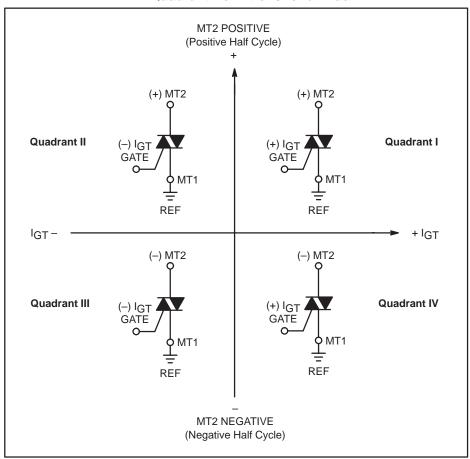
Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	•				
Peak Repetitive Blocking Current ( $V_D$ = Rated $V_{DRM}$ , $V_{RRM}$ ; Gate Open) $T_J = 25^{\circ}C$ $T_J = +125^{\circ}C$	I <sub>DRM</sub> , I <sub>RRM</sub>	_	_	10 2.0	μA mA
ON CHARACTERISTICS					
Peak On-State Voltage (I <sub>TM</sub> = ±14 A Peak; Pulse Width = 1 to 2 ms, Duty Cycle ≤ 2%)	VTM	<u> </u>	1.2	1.65	Volts
Gate Trigger Current (Continuous dc) (Main Terminal Voltage = 12 Vdc, R <sub>L</sub> = 100 Ohms)  MT2(+), G(+)  MT2(+), G(-)  MT2(-), G(-)  MT2(-), G(+)	l <sub>GT</sub>	_ _ _ _	12 12 20 35	50 50 50 75	mA
Gate Trigger Voltage (Continuous dc) (Main Terminal Voltage = 12 Vdc, R <sub>L</sub> = 100 Ohms) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(+)	VGT	_ _ _ _	0.9 0.9 1.1 1.4	2.0 2.0 2.0 2.5	Volts
Gate Non–Trigger Voltage (Continuous dc) (Main Terminal Voltage = 12 V, $R_L$ = 100 $\Omega$ , $T_J$ = +125°C) All Four Quadrants	V <sub>GD</sub>	0.2	_	_	Volts
Holding Current (Main Terminal Voltage = 12 Vdc, Gate Open, Initiating Current = ±200 mA)	lн	_	6.0	50	mA
Turn-On Time (Rated $V_{DRM}$ , $I_{TM}$ = 14 A, $I_{GT}$ = 120 mA, Rise Time = 0.1 $\mu$ s, Pulse Width = 2 $\mu$ s)	<sup>t</sup> gt	_	1.5	_	μs
DYNAMIC CHARACTERISTICS	•	•			
Critical Rate of Rise of Commutation Voltage ( $V_D$ = Rated $V_{DRM}$ , $I_{TM}$ = 14 A, Commutating di/dt = 5.0 A/ms, Gate Unenergized, $T_C$ = +70°C)	dv/dt(c)	_	5.0	-	V/μs
Critical Rate of Rise of Off–State Voltage ( $V_D$ = Rated $V_{DRM}$ , Exponential Voltage Rise, Gate Open, $T_C$ = +70°C)	dv/dt		100	_	V/μs

## Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
V <sub>DRM</sub>	Peak Repetitive Forward Off State Voltage
IDRM	Peak Forward Blocking Current
VRRM	Peak Repetitive Reverse Off State Voltage
I <sub>RRM</sub>	Peak Reverse Blocking Current
V <sub>TM</sub>	Maximum On State Voltage
lΗ	Holding Current



#### **Quadrant Definitions for a Triac**



All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.

#### **TYPICAL CHARACTERISTICS**

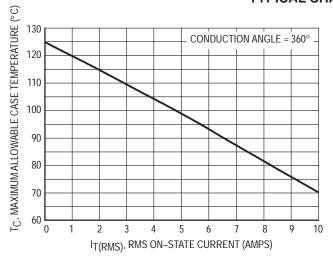


Figure 1. Current Derating

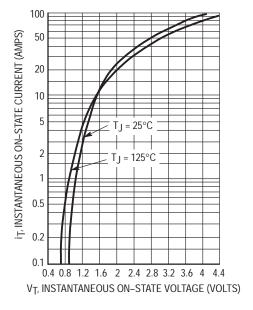


Figure 3. Maximum On-State Characteristics

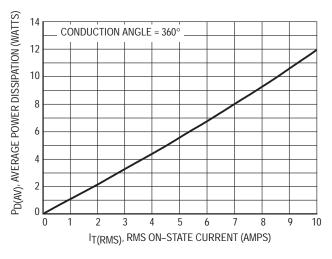
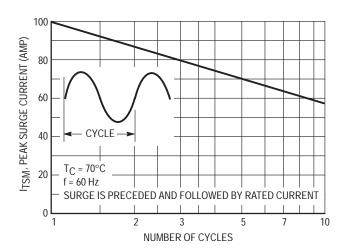


Figure 2. Power Dissipation



**Figure 4. Maximum Nonrepetitive Surge Current** 

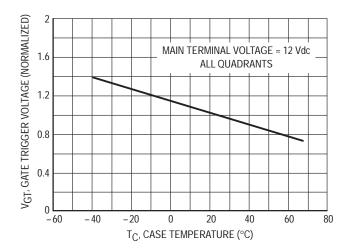
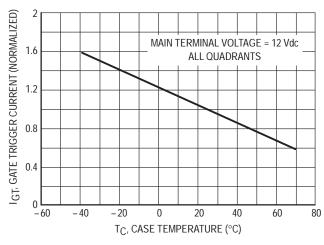
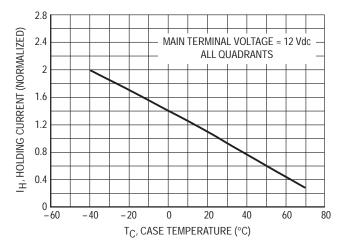


Figure 5. Typical Gate Trigger Voltage





**Figure 6. Typical Gate Trigger Current** 

Figure 7. Typical Holding Current

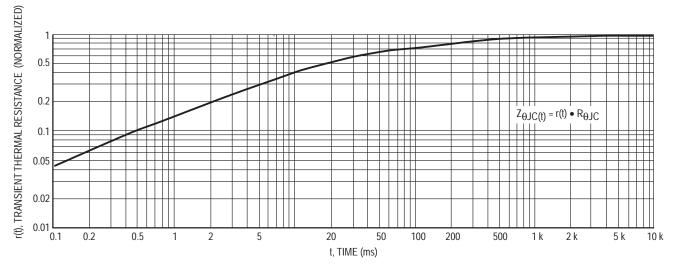
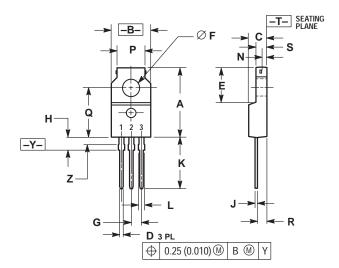


Figure 8. Thermal Response

#### **PACKAGE DIMENSIONS**

#### ISOLATED TO-220 Full Pack

CASE 221C-02 ISSUE C



- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: INCH.

  3. LEAD DIMENSIONS UNCONTROLLED WITHIN DIMENSION Z.

	INCHES MILLIMETER		IETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.680	0.700	17.28	17.78
В	0.388	0.408	9.86	10.36
С	0.175	0.195	4.45	4.95
D	0.025	0.040	0.64	1.01
Ε	0.340	0.355	8.64	9.01
F	0.140	0.150	3.56	3.81
G	0.100 BSC		2.54 BSC	
Н	0.110	0.155	2.80	3.93
J	0.018	0.028	0.46	0.71
K	0.500	0.550	12.70	13.97
L	0.045	0.070	1.15	1.77
N	0.049		1.25	
Р	0.270	0.290	6.86	7.36
Q	0.480	0.500	12.20	12.70
R	0.090	0.120	2.29	3.04
S	0.105	0.115	2.67	2.92
Z	0.070	0.090	1.78	2.28

STYLE 3: PIN 1. MT 1



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